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INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)		APPLICANT(S) Tomomi YAMANOBE	
		FILING DATE June 29, 2001	

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U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB CLASS
mc		JP 10-177991	30/6/1998	Japan		

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)

mc		"Process Degradation of a Ferroelectric Capacitor", Tamura et al., Denshijouhou Tuusin Gakkai Ronbunsi C Vol. J83-C No. 1, pp. 53-59 (2000).
mc		"Protection of SrBi ₂ Ta ₂ O ₉ ferroelectric capacitors from hydrogen damage by optimized metallization for memory applications" Hong et al., Applied Physics Letters, Vol. 77(1), July 3, 2000, pp.76-78, 2000 American Institute of Physics.

EXAMINER		DATE CONSIDERED 7/18/02
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